L Number	Hits	Search Text	DB	Time stamp
1	116440	wafer	USPAT	2004/04/30 15:14
2	60050	photoresist	USPAT	2004/04/30 15:14
3	146708	etching	USPAT	2004/04/30 15:14
4	14973	(monitor$3 or determin$6 or indicat$3 or detect$3) with (contamination or (dynamic adj particles) or pollut$3)	USPAT	2004/04/30 18:42
5	39898	(count$3 or measur$3) with ((dynamic adj particles) or particle)	USPAT	2004/04/30 19:53
6	3047	((silicon adj nitride) or (silicon adj oxide) or (silicon adj oxynitride) or polysilicon) adj2 etching	USPAT	2004/04/30 18:56
7	0	wafer and photoresist and etching and ((monitor$3 or determin$6 or indicat$3 or detect$3) with (contamination or (dynamic adj particles) or pollut$3)) and ((count$3 or measur$3) with ((dynamic adj particles) or particle)) and (((silicon adj nitride) or (silicon adj oxide) or (silicon adj oxynitride) or polysilicon) adj2 etching)	USPAT	2004/04/30 15:18
8	10981	wafer with photoresist	USPAT	2004/04/30 15:18
9	63	(wafer with photoresist) and ((monitor$3 or determin$6 or indicat$3 or detect$3) with (contamination or (dynamic adj particles) or pollut$3)) and ((count$3 or measur$3) with ((dynamic adj particles) or particle))	USPAT	2004/04/30 15:18
10	0	((wafer with photoresist) and ((monitor$3 or determin$6 or indicat$3 or detect$3) with (contamination or (dynamic adj particles) or pollut$3)) and ((count$3 or measur$3) with ((dynamic adj particles) or particle))) and (((silicon adj nitride) or (silicon adj oxide) or (silicon adj oxynitride) or polysilicon) adj2 etching)	USPAT	2004/04/30 15:19
11	23210	((silicon adj nitride) or (silicon adj oxide) or (silicon adj oxynitride) or polysilicon) with etching	USPAT	2004/04/30 18:17
12	4	((wafer with photoresist) and ((monitor$3 or determin$6 or indicat$3 or detect$3) with (contamination or (dynamic adj particles) or pollut$3)) and ((count$3 or measur$3) with ((dynamic adj particles) or particle))) and (((silicon adj nitride) or (silicon adj oxide) or (silicon adj oxynitride) or polysilicon) with etching)	USPAT	2004/04/30 16:17
13	250	((count$3 or measur$3) with ((dynamic adj particles) or particle)) and (wafer with photoresist)	USPAT	2004/04/30 15:47
14	4	(((count$3 or measur$3) with ((dynamic adj particles) or particle)) and (wafer with photoresist)) and (((silicon adj nitride) or (silicon adj oxide) or (silicon adj oxynitride) or polysilicon) adj2 etching)	USPAT	2004/04/30 15:47
15	340	15.ti,ab,clm.	USPAT	2004/04/30 16:17
16	0	(wafer with photoresist) and 15.ti,ab,clm. and (((silicon adj nitride) or (silicon adj oxide) or (silicon adj oxynitride) or polysilicon) with etching)	USPAT	2004/04/30 16:18
17	0	(wafer with photoresist) and 15.ti,ab,clm.	USPAT	2004/04/30 16:18
18	6	15.ti,ab,clm. and photoresist	USPAT	2004/04/30 16:18
19	5859	((count$3 or measur$3) with ((dynamic adj particles) or particle)).ti,ab,clm.	USPAT	2004/04/30 18:27
20	1708	((monitor$3 or determin$6 or indicat$3 or detect$3) with (contamination or (dynamic adj particles) or pollut$3)).ti,ab,clm.	USPAT	2004/04/30 16:20
21	2	(((monitor$3 or determin$6 or indicat$3 or detect$3) with (contamination or (dynamic adj particles) or pollut$3)).ti,ab,clm.) and (wafer with photoresist) and ((count$3 or measur$3) with ((dynamic adj particles) or particle))	USPAT	2004/04/30 18:16
32	0	(((count$3 or measur$3) with ((dynamic adj particles) or particle)).ti,ab,clm.) and (((silicon adj nitride) or (silicon adj oxide) or (silicon adj oxynitride) or polysilicon) adj2 etching)	USPAT	2004/04/30 19:50
34	2	((((count$3 or measur$3) with ((dynamic adj particles) or particle)).ti,ab,clm.) and (((silicon adj nitride) or (silicon adj oxide) or (silicon adj oxynitride) or polysilicon) with etching)) and photoresist	USPAT	2004/04/30 18:28
33	10	(((count$3 or measur$3) with ((dynamic adj particles) or particle)).ti,ab,clm.) and (((silicon adj nitride) or (silicon adj oxide) or (silicon adj oxynitride) or polysilicon) with etching)	USPAT	2004/04/30 18:29
35	0	(monitor$3 or determin$6 or indicat$3 or detect$3) with (contamination or (dynamic adj particles) or pollut$3) and 5837094.pn.	USPAT	2004/04/30 18:42
36	0	((silicon adj nitride) or (silicon adj oxide) or (silicon adj oxynitride) or polysilicon) and 6254398.pn.	USPAT	2004/04/30 18:57
37	2	(("3406289") or ("4571079")).PN.	USPAT	2004/04/30 19:34
38	76	wafer adj scanner	USPAT	2004/04/30 19:35

39	10	(wafer adj scanner).ti,ab,clm.	USPAT	2004/04/30 19:36
41	1	((wafer adj scanner).ti,ab,clm.) and ((count$3 or measur$3) with ((dynamic adj particles) or particle))	USPAT	2004/04/30 19:37
40	12	(wafer adj scanner) and ((count$3 or measur$3) with ((dynamic adj particles) or particle))	USPAT	2004/04/30 19:45
42	1	(wafer adj scanner) and ((count$3 or measur$3) with ((dynamic adj particles) or particle)) and photoresist	USPAT	2004/04/30 19:45
43	95	(((count$3 or measur$3) with ((dynamic adj particles) or particle)).ti,ab,clm.) and photoresist	USPAT	2004/04/30 19:50
44	61	((((count$3 or measur$3) with ((dynamic adj particles) or particle)).ti,ab,clm.) and photoresist) and wafer	USPAT	2004/04/30 19:53
45	2	(((((count$3 or measur$3) with ((dynamic adj particles) or particle)).ti,ab,clm.) and photoresist) and wafer) and (((silicon adj nitride) or (silicon adj oxide) or (silicon adj oxynitride) or polysilicon) with etching)	USPAT	2004/04/30 19:51
46	2	((((((count$3 or measur$3) with ((dynamic adj particles) or particle)).ti,ab,clm.) and photoresist) and wafer) and (((silicon adj nitride) or (silicon adj oxide) or (silicon adj oxynitride) or polysilicon) with etching)) and ((count$3 or measur$3) with ((dynamic adj particles) or particle))	USPAT	2004/04/30 19:53